

Appl. No. : 10/074,633  
Filed : February 11, 2002

IN THE SPECIFICATION:

Please replace paragraph [0001] with the following rewritten paragraph:

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[0001] This application claims priority to U.S. Provisional Application No. 60/268,337, filed February 12, 2001; U.S. Provisional Application No. 60/279,256, filed March 27, 2001; U.S. Provisional Application No. 60/311,609, filed August 9, 2001; U.S. Provisional Application No. 60/323,649, filed September 19, 2001; U.S. Provisional Application No. 60/332,696, filed November 13, 2001; U.S. Provisional Application No. 60/333,724, filed November 28, 2001; and U.S. Provisional Application No. 60/340,454, filed December 7, 2001; all of which are hereby incorporated by reference in their entireties. This application is also related to, and incorporates by reference in their entireties, co-owned and co-pending U.S. Patent Application Serial Numbers: 10/074,563; 10/074,149; 10/074,722; 10/074,564; and 10/074,534, all of which were filed on February 11, 2002.

Please delete paragraph [0002].

IN THE CLAIMS:

Please amend Claim 19 as follows:

19. (Amended) A high-rate deposition method comprising:
- Q2  
delivering trisilane to a mixed substrate surface under chemical vapor deposition conditions, at a delivery rate of at least about 0.001 milligrams per minute per square centimeter of the mixed substrate surface; and
- depositing a silicon-containing material onto the mixed substrate surface at a rate of about 10 Å per minute or greater.